

● General Description

The AGM30P55D1 combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

This device is ideal for load switch and battery protection applications.

● Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

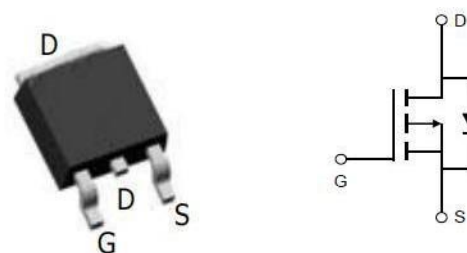
● Application

- MB/VGA Vcore
- SMPS 2nd Synchronous Rectifier
- POL application
- BLDC Motor driver

Product Summary

BVDSS	RDSON	ID
-30V	6.5mΩ	-65A

TO-252 Pin Configuration



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
AGM30P55D1	AGM30P55D1	TO-252	----	----	2500

Table 1. Absolute Maximum Ratings (TA=25°C)

Symbol	Parameter	Value	Unit
VDS	Drain-Source Voltage (VGS=0V)	-30	V
VGS	Gate-Source Voltage (VDS=0V)	±20	V
ID	Drain Current-Continuous(Tc=25°C) (Note 1)	-65	A
	Drain Current-Continuous(Tc=100°C)	--	A
IDM (pluse)	Drain Current-Continuous@ Current-Pulsed (Note 2)	-130	A
PD	Maximum Power Dissipation(Tc=25°C)	55	w
	Maximum Power Dissipation(Tc=125°C)	--	w
EAS	Avalanche energy (Note 3)	120	mJ
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 To 150	°C

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
RθJA	Thermal Resistance Junction-ambient (Steady State) ¹	---	50	°C/W
RθJC	Thermal Resistance Junction-Case ¹	---	2.1	°C/W

Table 3. Electrical Characteristics (TA=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BVDSS	Drain-Source Breakdown Voltage	VGS=0V ID=250μA	-30	--	--	V
IDSS	Zero Gate Voltage Drain Current	VDS=-30V,VGS=0V	--	--	-1.0	μA
IGSS	Gate-Body Leakage Current	VGS=±20V,VDS=0V	--	--	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS,ID=-250μA	-1.2	-1.5	-2.5	V
gFS	Forward Transconductance	VDS=-10V,ID=-5A	12	--	--	S
RDS(on)	Drain-Source On-State Resistance	VGS=-10V, ID=-20A	--	6.5	8.5	mΩ
		VGS=-4.5V, ID=-10A	--	10	12.5	mΩ
Dynamic Characteristics						
Ciss	Input Capacitance	F=1MHZ	--	3050	--	pF
Coss	Output Capacitance		--	460	--	pF
Crss	Reverse Transfer Capacitance		--	240	--	pF
Rg	Gate resistance	VGS=0V, VDS=-0V,f=1.0MHz	--	--	--	Ω
Switching Times						
td(on)	Turn-on Delay Time	VGS=10V,VDS=20V, ID=30A,RGEN=3Ω	--	--	--	nS
tr	Turn-on Rise Time		--	--	--	nS
td(off)	Turn-Off Delay Time		--	--	--	nS
tf	Turn-Off Fall Time		--	--	--	nS
Qg	Total Gate Charge	VGS=-10V, VDS=-25V, ID=-15A	--	28	--	nC
Qgs	Gate-Source Charge		--	9.5	--	nC
Qgd	Gate-Drain Charge		--	10.6	--	nC
Source-Drain Diode Characteristics						
ISD	Source-Drain Current(Body Diode)		--	--	--	A
VSD	Forward on Voltage	VGS=0V,IS=-10A	--	--	--	V
trr	Reverse Recovery Time	IF=-25A , dI/dt=100A/μs , TJ=25°C	--	--	--	ns
Qrr	Reverse Recovery Charge		--	--	--	nc

Notes 1.The maximum current rating is package limited.

Notes 2.Repetitive Rating: Pulse width limited by maximum junction temperature

Notes 3.EAS condition: TJ=25°C,VDD=15V,VG=10V, RG=25Ω

Fig.1 Power Dissipation Derating Curve

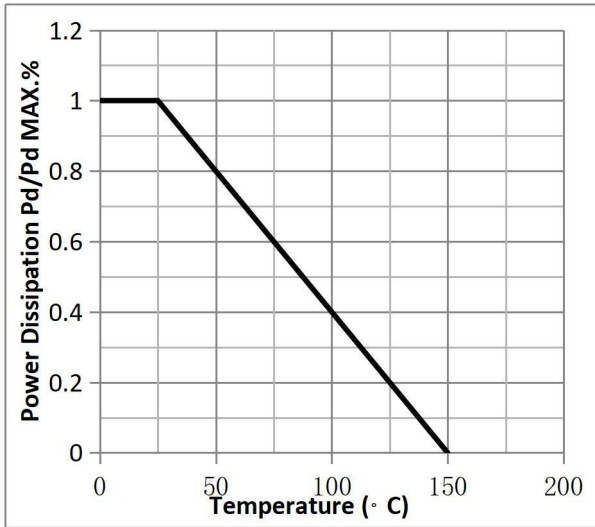


Fig.2 Typical output Characteristics

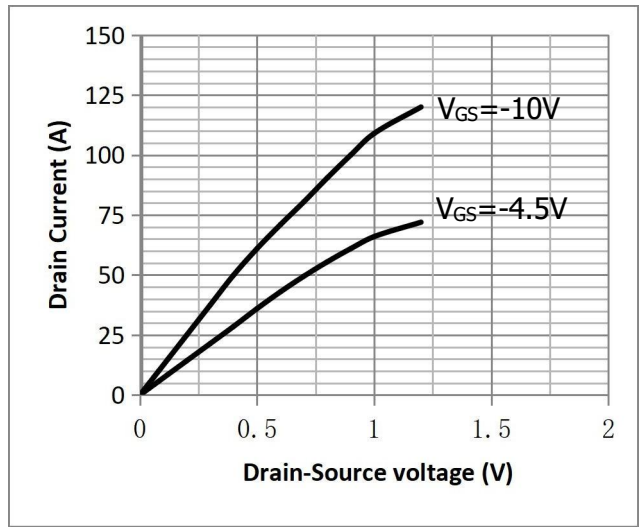


Fig.3 Threshold Voltage V.S Junction Temperature

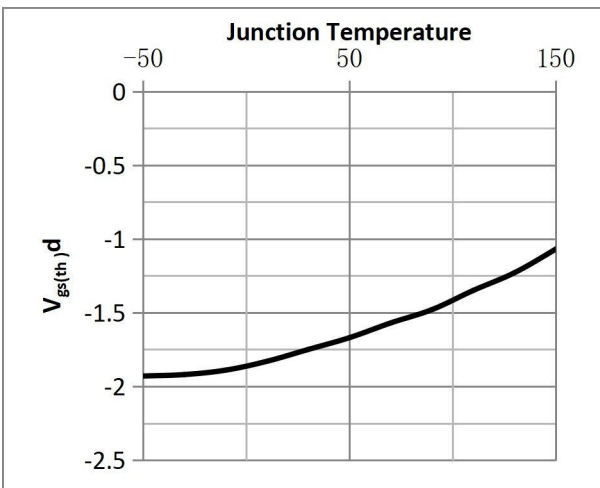


Fig.4 Resistance V.S Drain Current

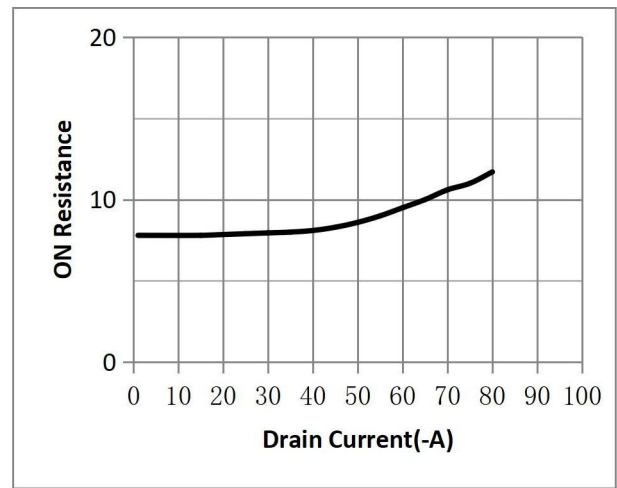


Fig.5 On-Resistance VS Gate Source Voltage

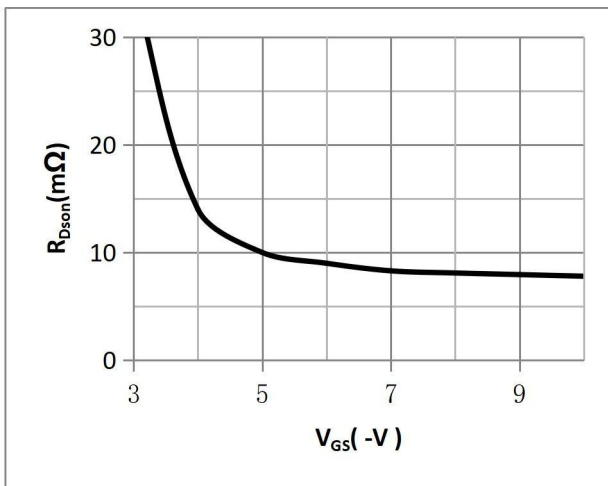


Fig.6 On-Resistance V.S Junction Temperature

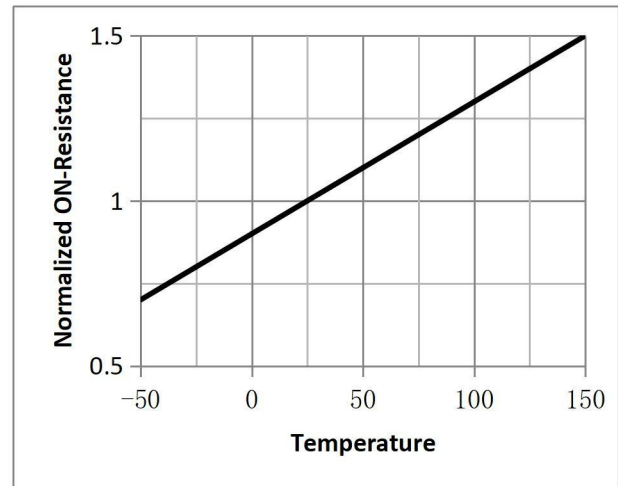


Fig.7 Switching Time Measurement Circuit

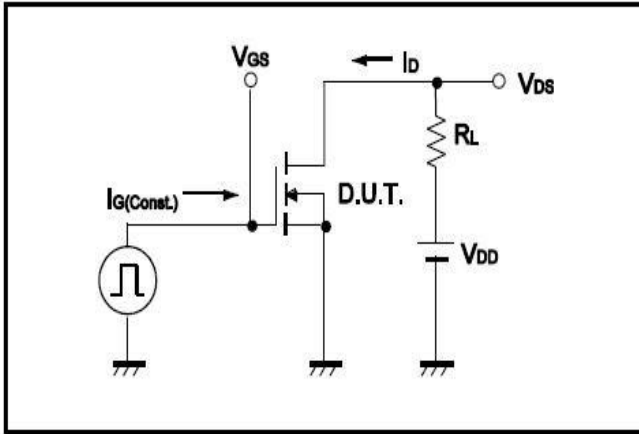


Fig.8 Gate Charge Waveform

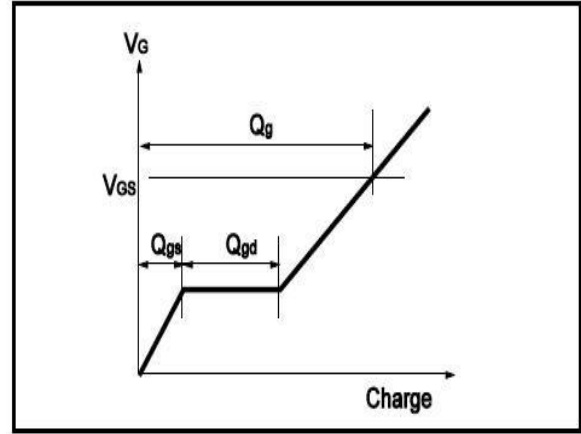


Fig.9 Switching Time Measurement Circuit

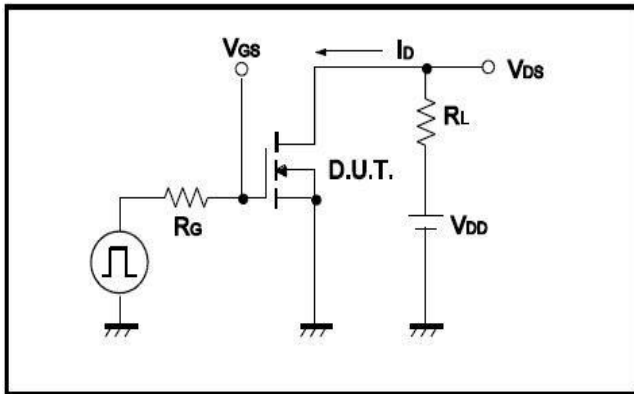


Fig.10 Gate Charge Waveform

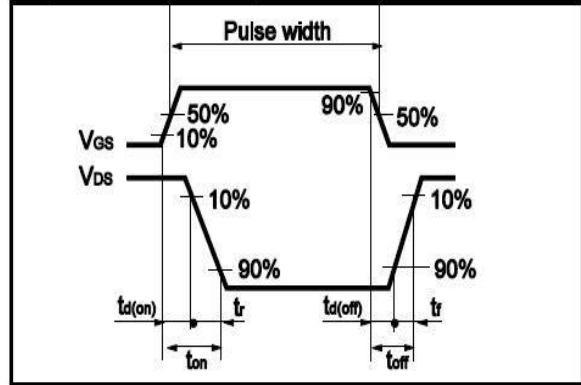


Fig.11 Avalanche Measurement Circuit

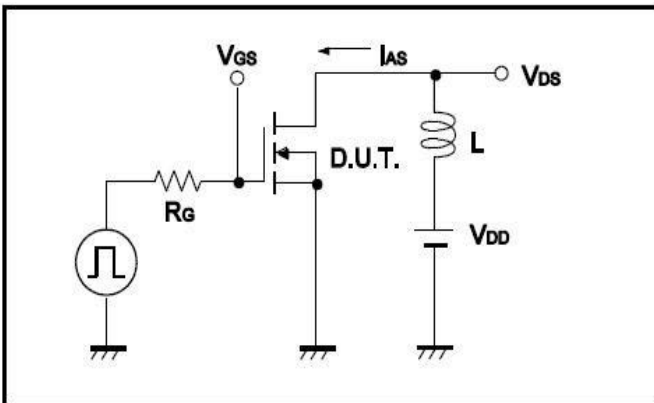
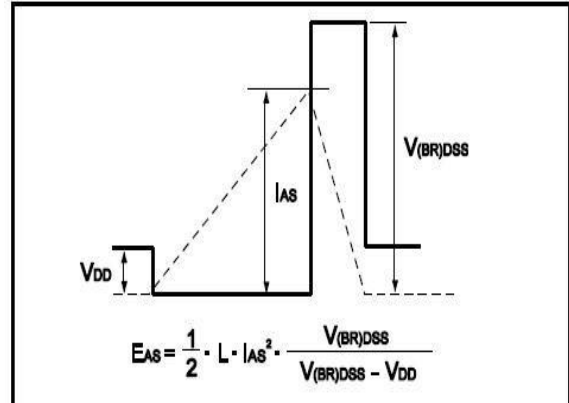
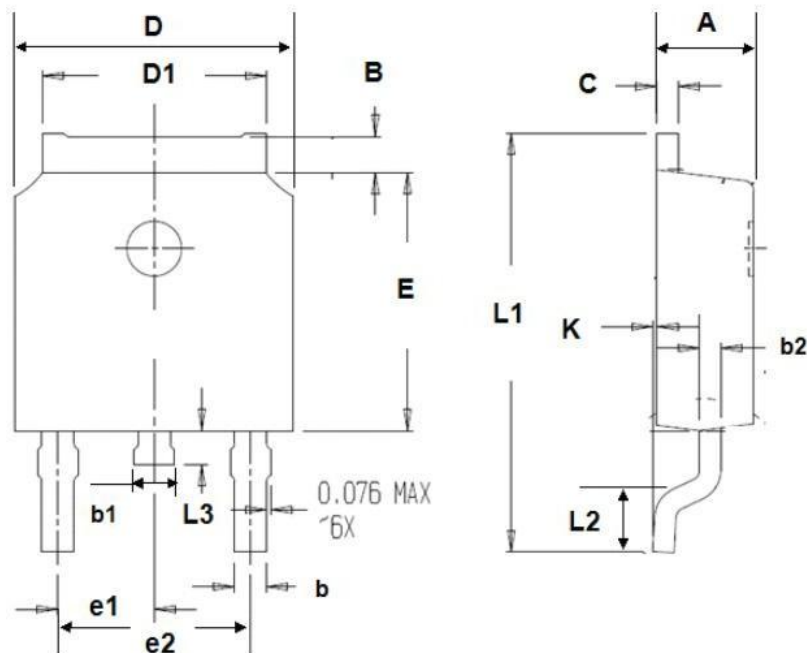


Fig.12 Avalanche Waveform



•Dimensions

SYMBOL	min	max	SYMBOL	min	max
A	2.10	2.50	B	0.85	1.25
b	0.50	0.80	b1	0.50	0.90
b2	0.45	0.70	C	0.45	0.70
D	6.30	6.75	D1	5.10	5.50
E	5.30	6.30	e1	2.25	2.35
L1	9.20	10.60	e2	4.45	4.75
L2	0.90	1.75	L3	0.60	1.10
K	0.00	0.23			




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